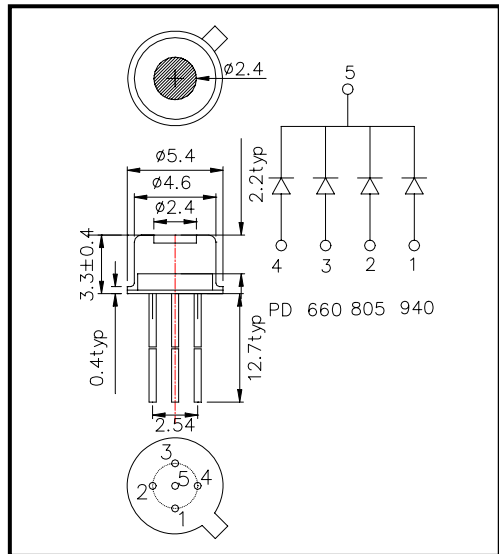


L660/805/940/PD010-35B52 multi-wavelength LED

L660/805/940/PD010-35B52 consists of an AlGaAs'(660, 805nm), GaAs'(940nm) LED and a Si-PD mounted on TO-18 stem hermetical sealed with a Flat glass lens, and is designed to monitor reflected light through detector for controlling its own output power

◆ Outer dimension (Unit: mm)



◆ Specifications

- 1) Product Name multi-wavelength LED Lamp
- 2) Type No. L660/805/940/PD010-35B52
- 3) Chip
 - (1) Chip material AlGaAs, GaAs, Si-PIN-PD
 - (2) Peak wavelength 660, 805, 940nm
- 4) Package
 - (1) Stem TO-18 5pin type
 - (2) Lens Φ 2.4mm Flat glass

◆ Absolute Maximum Ratings [Ta=25°C]

Item	Symbol	Maximum Rated Value			Unit	
		660	805	940		
Power Dissipation	PD	120	170	140	mW	
Forward Current	IF	50	100	100	mA	
Pulse Forward Current	IF	200	500	1000	mA	
Reverse Voltage	VR	5			100	V
Operating Temperature	TOPR	-30 ~ +85			°C	
Storage Temperature	TSTG	-30 ~ +100			°C	
Soldering Temperature	TSOL	260			°C	

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C and is allowed in the area apart 3mm from the bottom of the lamp.

◆ Electro-Optical Characteristics [Ta=25°C]

Symbol	Wavelength	Condition	Minimum	Typical	Maximum	Unit
VF	660	IF=20mA		1.9	2.2	V
	805			1.5	1.7	
	940			1.2	1.3	
IR		VR=5V			10	uA
PO	660	IF=20mA		2.9		mW
	805			3.5		
	940			2.5		
λ P	660	IF=20mA	650	660	670	nm
	805		795	805	915	
	940		935	940	955	
$\Delta\lambda$	660	IF=20mA		20		nm
	805			30		
	940			45		
IL	660	VR=10V		50		uA
	805			130		
	940			140		
ID	PD	VR=10V			10	nA

‡Total Radiated Power is measured by Photodyne #500